

LT1055/LT1056

ABSOLUTE MAXIMUM RATINGS (Note 1)

Supply Voltage	±20V	LT1055AC/LT1055C/LT1056AC/	
Differential Input Voltage	±40V	LT1056C	0°C to 70°C
Input Voltage	±20V	Storage Temperature Range	
Output Short-Circuit Duration	Indefinite	All Devices	–65°C to 150°C
Operating Temperature Range		Lead Temperature (Soldering, 10 sec).....	300°C
LT1055AM/LT1055M/LT1056AM/			
LT1056M (OBSOLETE)	–55°C to 125°C		

PIN CONFIGURATION

TOP VIEW

N8 PACKAGE
8-LEAD PDIP
 $T_{JMAX} = 150^{\circ}C, \theta_{JA} = 130^{\circ}C/W$

TOP VIEW

S8 PACKAGE
8-LEAD PLASTIC SO
 $T_{JMAX} = 150^{\circ}C, \theta_{JA} = 130^{\circ}C/W$

TOP VIEW

H PACKAGE
8-LEAD TO-5 METAL CAN
 $T_{JMAX} = 150^{\circ}C, \theta_{JA} = 150^{\circ}C/W, \theta_{JC} = 45^{\circ}C/W$

OBSOLETE PACKAGE
Consider the N8 for Alternate Source

ORDER INFORMATION

LEAD FREE FINISH	TAPE AND REEL	PART MARKING	PACKAGE DESCRIPTION	TEMPERATURE RANGE
LT1055CN8#PBF	LT1055CN8#TRPBF	LT1055CN8	8-Lead PDIP	0°C to 70°C
LT1056CN8#PBF	LT1056CN8#TRPBF	LT1056CN8	8-Lead PDIP	0°C to 70°C
LT1055S8#PBF	LT1055S8#TRPBF	1055	8-Lead Plastic SO	0°C to 70°C
LT1056S8#PBF	LT1056S8#TRPBF	1056	8-Lead Plastic SO	0°C to 70°C
OBSOLETE PACKAGE				
LT1055ACH#PBF	LT1055ACH#TRPBF	LT1055ACH	8-Lead TO-5 Metal Can	0°C to 70°C
LT1055CH#PBF	LT1055CH#TRPBF	LT1055CH	8-Lead TO-5 Metal Can	0°C to 70°C
LT1055AMH#PBF	LT1055AMH#TRPBF	LT1055AMH	8-Lead TO-5 Metal Can	-55°C to 125°C
LT1055MH#PBF	LT1055MH#TRPBF	LT1055MH	8-Lead TO-5 Metal Can	-55°C to 125°C
LT1056ACH#PBF	LT1056ACH#TRPBF	LT1056ACH	8-Lead TO-5 Metal Can	0°C to 70°C
LT1056CH#PBF	LT1056CH#TRPBF	LT1056CH	8-Lead TO-5 Metal Can	0°C to 70°C
LT1056AMH#PBF	LT1056AMH#TRPBF	LT1056AMH	8-Lead TO-5 Metal Can	-55°C to 125°C
LT1056MH#PBF	LT1056MH#TRPBF	LT1056MH	8-Lead TO-5 Metal Can	-55°C to 125°C

Consult LTC Marketing for parts specified with wider operating temperature ranges.

Consult LTC Marketing for information on nonstandard lead based finish parts.

For more information on lead free part markings, go to: <http://www.linear.com/leadfree/>

For more information on tape and reel specifications, go to: <http://www.linear.com/tapeandreel/>

ELECTRICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{V}$, $V_{CM} = 0\text{V}$ unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	LT1055AM/LT1056AM LT1055AC/LT1056AC			LT1055M/LT1056M LT1055CH/LT1056CH LT1055CN8/LT1056CN8			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OS}	Input Offset Voltage (Note 2)	LT1055 H Package LT1056 H Package LT1055 N8 Package LT1056 N8 Package		50 50	150 180		70 70 120 140	400 450 700 800	μV μV μV μV
I_{OS}	Input Offset Current	Fully Warmed Up		2	10		2	20	pA
I_B	Input Bias Current	Fully Warmed Up $V_{CM} = 10\text{V}$		± 10 30	± 50 130		± 10 30	± 50 150	pA pA
	Input Resistance: Differential	Common Mode $V_{CM} = -11\text{V}$ to 8V $V_{CM} = 8\text{V}$ to 11V		10^{12}			10^{12}		Ω
				10^{12}			10^{12}		Ω
				10^{11}			10^{11}		Ω
	Input Capacitance			4			4		pF
e_n	Input Noise Voltage	0.1Hz to 10Hz LT1055 LT1056		1.8 2.5			2.0 2.8		μV_{P-P} μV_{P-P}
	Input Noise Voltage Density	$f_0 = 10\text{Hz}$ (Note 3) $f_0 = 1\text{kHz}$ (Note 4)		28 14	50 20		30 15	60 22	$\text{nV}/\sqrt{\text{Hz}}$ $\text{nV}/\sqrt{\text{Hz}}$
I_n	Input Noise Current Density	$f_0 = 10\text{Hz}$, 1kHz (Note 5)		1.8	4		1.8	4	$\text{fA}/\sqrt{\text{Hz}}$
A_{VOL}	Large-Signal Voltage Gain	$V_O = \pm 10\text{V}$ $R_L = 2\text{k}$ $R_L = 1\text{k}$	150 130	400 300		120 100	400 300		V/mV V/mV
	Input Voltage Range		± 11	± 12		± 11	± 12		V
CMRR	Common Mode Rejection Ratio	$V_{CM} = \pm 11\text{V}$	86	100		83	98		dB
PSRR	Power Supply Rejection Ratio	$V_S = \pm 10\text{V}$ to $\pm 18\text{V}$	90	106		88	104		dB
V_{OUT}	Output Voltage Swing	$R_L = 2\text{k}$	± 12	± 13.2		± 12	± 13.2		V

10556fd

LT1055/LT1056

ELECTRICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$. $V_S = \pm 15\text{V}$, $V_{CM} = 0\text{V}$ unless otherwise noted.†

SYMBOL	PARAMETER	CONDITIONS	LT1055AM/LT1056AM LT1055AC/LT1056AC			LT1055M/LT1056M LT1055CH/LT1056CH LT1055CN8/LT1056CN8			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew Rate	LT1055 LT1056	10 12	13 16		7.5 9.0	12 14		V/ μs V/ μs
GBW	Gain Bandwidth Product	f = 1MHz LT1055 LT1056		5.0 6.5			4.5 5.5		MHz MHz
I _S	Supply Current	LT1055 LT1056		2.8 5.0	4.0 6.5		2.8 5.0	4.0 7.0	mA mA
	Offset Voltage Adjustment Range	R _{POT} = 100k		±5			±5		mV

The ● denotes the specifications which apply over the temperature range $0^\circ\text{C} \leq T_A \leq 70^\circ\text{C}$. $V_S = \pm 15\text{V}$, $V_{CM} = 0\text{V}$ unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS		LT1055AC LT1056AC			LT1055CH/LT1056CH LT1055CN8/LT1056CN8			UNITS
				MIN	TYP	MAX	MIN	TYP	MAX	
V _{OS}	Input Offset Voltage (Note 2)	LT1055 H Package LT1056 H Package LT1055 N8 Package LT1056 N8 Package	● ● ● ●		100 100	330 360		140 140 250 280	750 800 1250 1350	μV μV μV μV
	Average Temperature Coefficient of Input Offset Voltage	H Package (Note 6) N8 Package (Note 6)	● ●		1.2	4.0		1.6 3.0	8.0 12.0	$\mu\text{V}/^\circ\text{C}$ $\mu\text{V}/^\circ\text{C}$
I _{OS}	Input Offset Current	Warmed Up $T_A = 70^\circ\text{C}$	● ●		10 14	50 70		16 18	80 100	pA pA
I _B	Input Bias Current	Warmed Up $T_A = 70^\circ\text{C}$	● ●		±30 ±40	±150 ±80		±40 ±50	±200 ±240	pA pA
A _{VOL}	Large-Signal Voltage Gain	V _O = ±10V, R _L = 2k	●	80	250		60	250		V/mV
CMRR	Common Mode Rejection Ratio	V _{CM} = ±10.5V	●	85	100		82	98		dB
PSRR	Power Supply Rejection Ratio	V _S = ±10V to ±18V	●	89	105		87	103		dB
V _{OUT}	Output Voltage Swing	R _L = 2k	●	±12	±13.1		±12	±13.1		V

The ● denotes the specifications which apply over the temperature range $-55^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$. $V_S = \pm 15\text{V}$, $V_{CM} = 0\text{V}$, unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS		LT1055AM LT1056AM			LT1055M LT1056M			UNITS
				MIN	TYP	MAX	MIN	TYP	MAX	
V _{OS}	Input Offset Voltage (Note 2)	LT1055 LT1056	● ●		180 180	500 550		250 250	1200 1250	μV μV
	Average Temperature Coefficient of Input Offset Voltage	(Note 6)	●		1.3	4.0		1.8	8.0	$\mu\text{V}/^\circ\text{C}$
I _{OS}	Input Offset Current	Warmed Up $T_A = 125^\circ\text{C}$	● ●		0.20 0.25	1.2 1.5		0.25 0.30	1.8 2.4	nA nA
I _B	Input Bias Current	Warmed Up $T_A = 125^\circ\text{C}$	● ●		±0.4 ±0.5	±2.5 ±3.0		±0.5 ±0.6	±4.0 ±5.0	nA nA
A _{VOL}	Large-Signal Voltage Gain	V _O = ±10V, R _L = 2k	●	40	120		35	120		V/mV
CMRR	Common Mode Rejection Ratio	V _{CM} = ±10.5V	●	85	100		82	98		dB
PSRR	Power Supply Rejection Ratio	V _S = ±10V to ±17V	●	88	104		86	102		dB
V _{OUT}	Output Voltage Swing	R _L = 2k	●	±12	±12.9		±12	±12.9		V

10556fd

ELECTRICAL CHARACTERISTICS

$T_A = 25^\circ\text{C}$. $V_S = \pm 15\text{V}$, $V_{CM} = 0\text{V}$ unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	LT1055CS8/LT1056CS8			UNITS
			MIN	TYP	MAX	
V_{OS}	Input Offset Voltage (Note 2)			500	1500	μV
I_{OS}	Input Offset Current	Fully Warmd Up		5	30	pA
I_B	Input Bias Current	Fully Warmd Up $V_{CM} = 10\text{V}$		± 30 30	± 100 150	pA pA
	Input Resistance Differential	$V_{CM} = -11\text{V}$ to 8V $V_{CM} = 8\text{V}$ to 11V		0.4		$\text{T}\Omega$
	Common Mode			0.4		$\text{T}\Omega$
				0.05		$\text{T}\Omega$
	Input Capacitance			4		pF
e_n	Input Noise Voltage	0.1Hz to 10Hz LT1055 LT1056		2.5 3.5		μV_{P-P} μV_{P-P}
	Input Noise Voltage Density	$f_0 = 10\text{Hz}$ (Note 4) $f_0 = 1\text{kHz}$ (Note 4)		35 15	70 22	$\text{nV}/\sqrt{\text{Hz}}$ $\text{nV}/\sqrt{\text{Hz}}$
i_n	Input Noise Current Density	$f_0 = 10\text{Hz}$, 1kHz (Note 5)		2.5	10	$\text{fA}/\sqrt{\text{Hz}}$
A_{VOL}	Large-Signal Voltage Gain	$V_0 = \pm 10\text{V}$ $R_L = 2\text{k}$ $R_L = 1\text{k}$	120 100	400 300		V/mV V/mV
	Input Voltage Range		± 11	± 12		V
CMRR	Common Mode Rejection Ratio	$V_{CM} = \pm 11\text{V}$	83	98		dB
PSRR	Power Supply Rejection Ratio	$V_S = \pm 10\text{V}$ to $\pm 18\text{V}$	88	104		dB
V_{OUT}	Output Voltage Swing	$R_L = 2\text{K}$	± 12	± 13.2		V
SR	Slew Rate	LT1055 LT1056	7.5	12		$\text{V}/\mu\text{s}$
			9.0	14		$\text{V}/\mu\text{s}$
GBW	Gain Bandwidth Product	$f = 1\text{MHz}$ LT1055 LT1056		4.5		MHz
				5.5		MHz
I_S	Supply Current	LT1055 LT1056		2.8	4.0	mA
				5.0	7.0	mA
	Offset Voltage Adjustment Range	$R_{POT} = 100\text{k}$		± 5		mV

The ● denotes the specifications which apply over the temperature range $0^\circ\text{C} \leq T_A \leq 70^\circ\text{C}$. $V_S = \pm 15\text{V}$, $V_{CM} = 0\text{V}$ unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS		LT1055CS8/LT1056CS8			UNITS
				MIN	TYP	MAX	
V_{OS}	Input Offset Voltage (Note 2)		●		800	2200	μV
	Average Temperature Coefficient of Input Offset Voltage		●		4	15	$\mu\text{V}/^\circ\text{C}$
I_{OS}	Input Offset Current	Warmd Up, $T_A = 70^\circ\text{C}$	●		18	150	pA
I_B	Input Bias Current	Warmd Up, $T_A = 70^\circ\text{C}$	●		± 60	± 400	pA
A_{VOL}	Large-Signal Voltage Gain	$V_0 = \pm 10\text{V}$, $R_L = 2\text{k}$	●	60	250		V/mV
CMRR	Common Mode Rejection Ratio	$V_{CM} = \pm 10.5\text{V}$	●	82	98		dB
PSRR	Power Supply Rejection Ratio	$V_S = \pm 10\text{V}$ to $\pm 18\text{V}$	●	87	103		dB
V_{OUT}	Output Voltage Swing	$R_L = 2\text{K}$	●	± 12	± 13.1		V

ELECTRICAL CHARACTERISTICS

For MIL-STD components, please refer to LTC883 data sheet for test listing and parameters.

Note 1: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

Note 2: Offset voltage is measured under two different conditions: (a) approximately 0.5 seconds after application of power; (b) at $T_A = 25^\circ\text{C}$ only, with the chip heated to approximately 38°C for the LT1055 and to 45°C for the LT1056, to account for chip temperature rise when the device is fully warmed up.

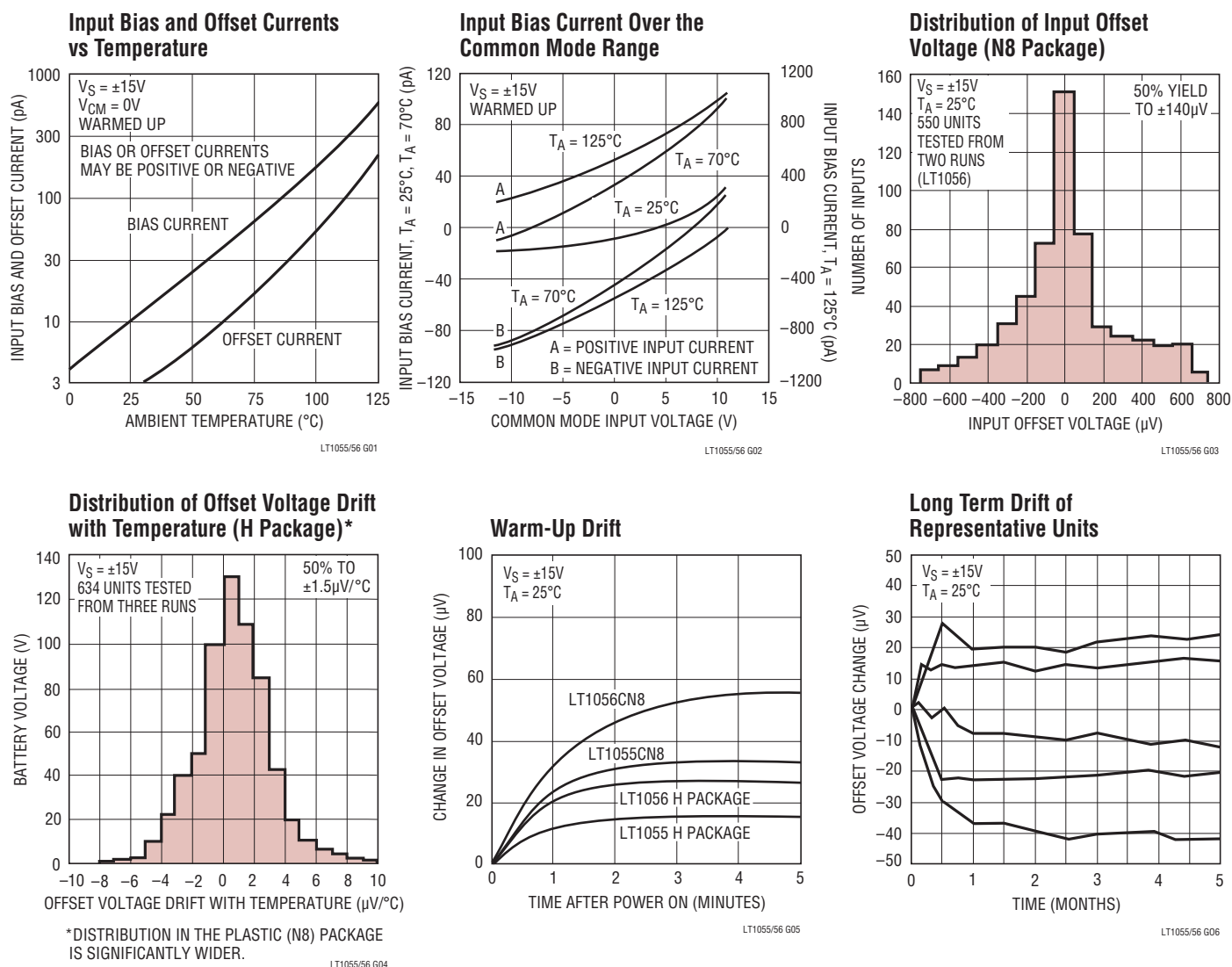
Note 3: 10Hz noise voltage density is sample tested on every lot of A grades. Devices 100% tested at 10Hz are available on request.

Note 4: This parameter is tested on a sample basis only.

Note 5: Current noise is calculated from the formula: $i_n = (2qI_B)^{1/2}$, where $q = 1.6 \cdot 10^{-19}$ coulomb. The noise of source resistors up to $1\text{G}\Omega$ swamps the contribution of current noise.

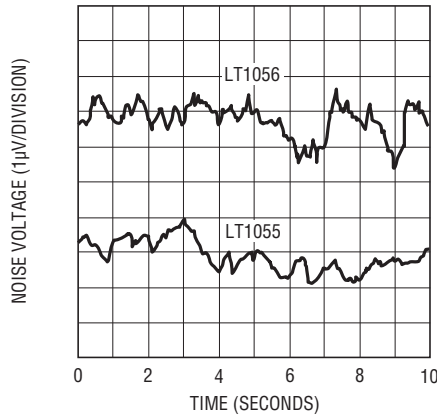
Note 6: Offset voltage drift with temperature is practically unchanged when the offset voltage is trimmed to zero with a 100k potentiometer between the balance terminals and the wiper tied to V^+ . Devices tested to tighter drift specifications are available on request.

TYPICAL PERFORMANCE CHARACTERISTICS

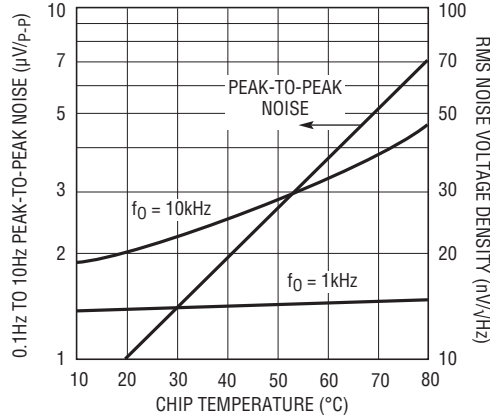


TYPICAL PERFORMANCE CHARACTERISTICS

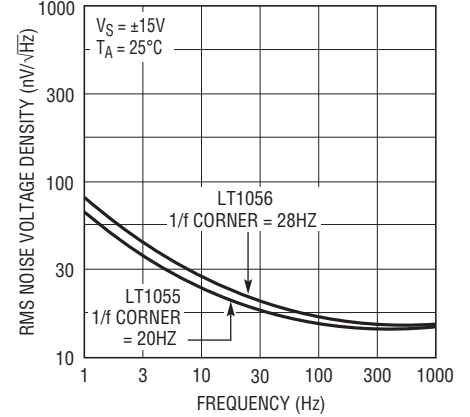
0.1Hz to 10Hz Noise



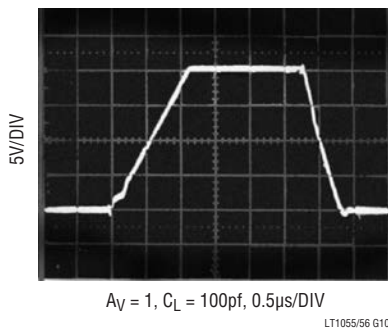
Noise vs Chip Temperature



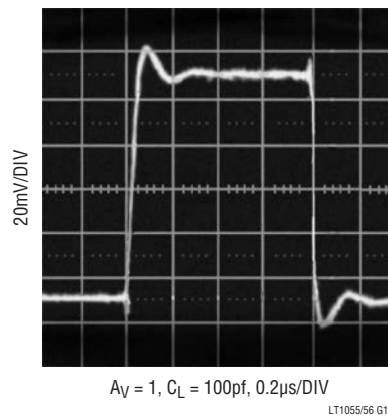
Voltage Noise vs Frequency



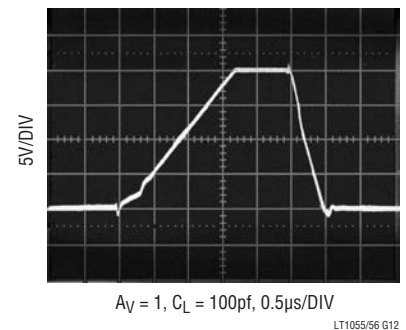
LT1056 Large-Signal Response



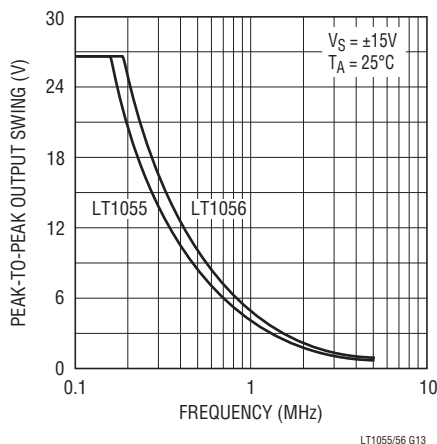
Small-Signal Response



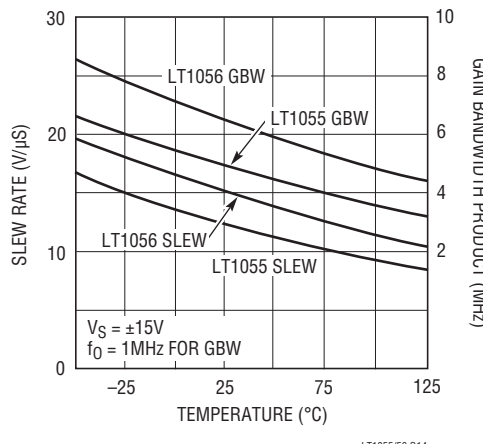
LT1055 Large-Signal Response



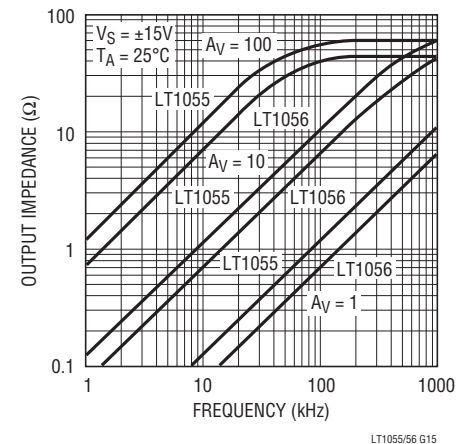
Undistorted Output Swing vs Frequency



Slew Rate, Gain Bandwidth vs Temperature

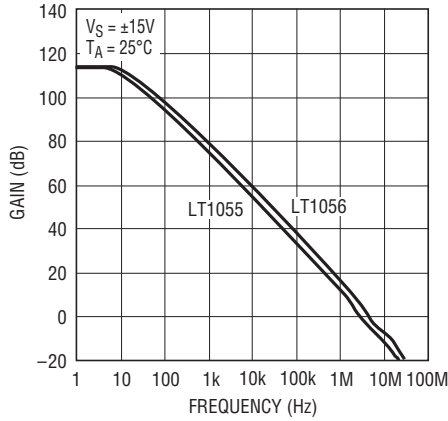


Output Impedance vs Frequency



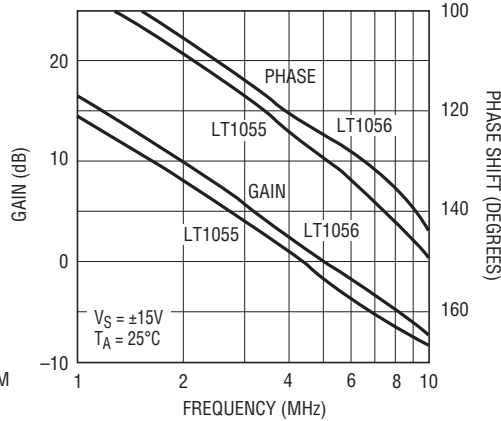
TYPICAL PERFORMANCE CHARACTERISTICS

Gain vs Frequency



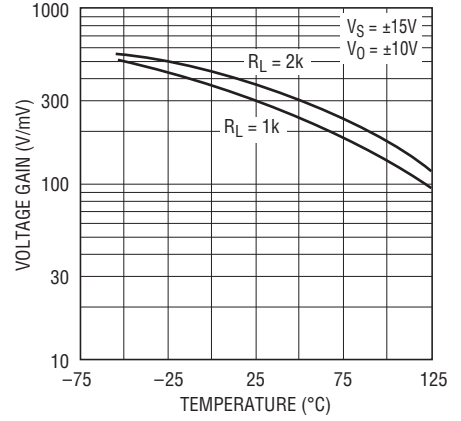
LT1055/56 G16

Gain, Phase Shift vs Frequency



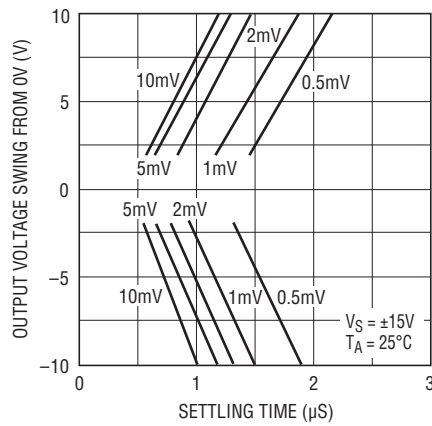
LT1055/56 G17

Voltage Gain vs Temperature



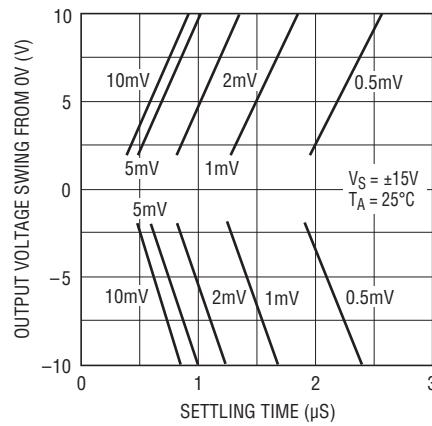
LT1055/56 G18

LT1055 Settling Time



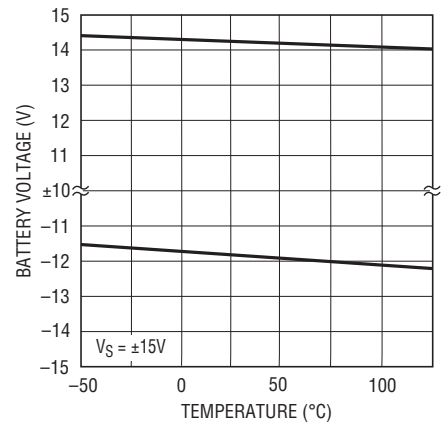
LT1055/56 G19

LT1056 Settling Time



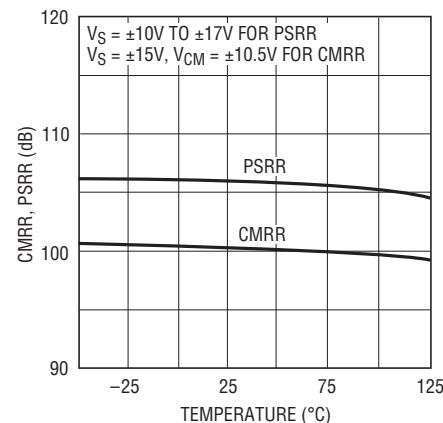
LT1055/56 G20

Common Mode Range vs Temperature



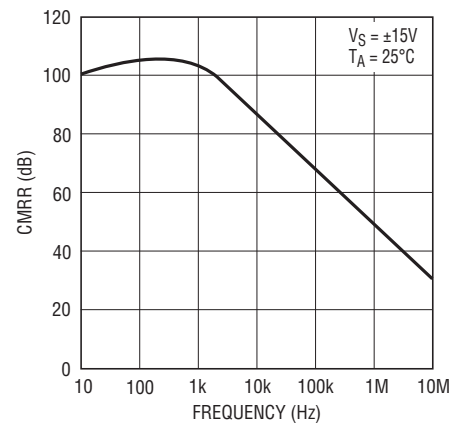
LT1055/56 G21

Common Mode and Power Supply Rejections vs Temperature



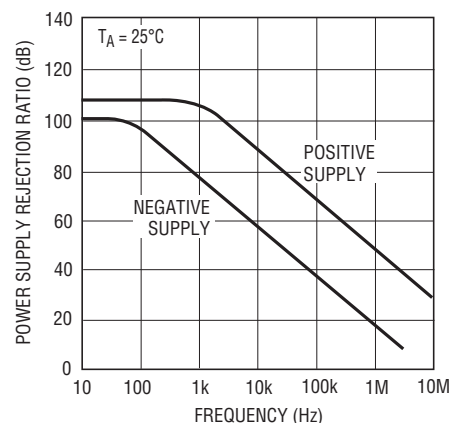
LT1055/56 G22

Common Mode Rejection Ratio vs Frequency



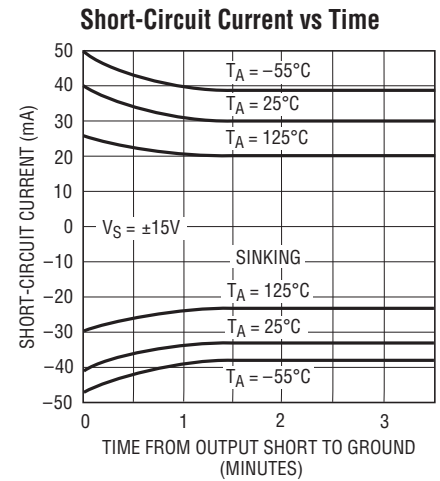
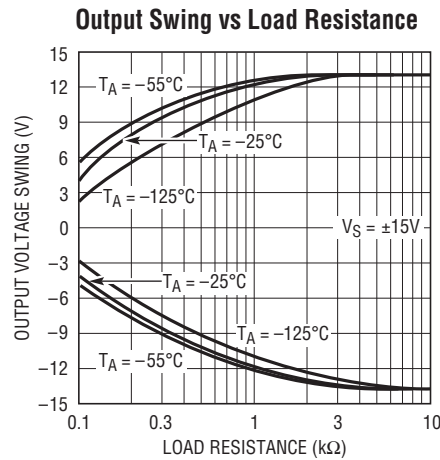
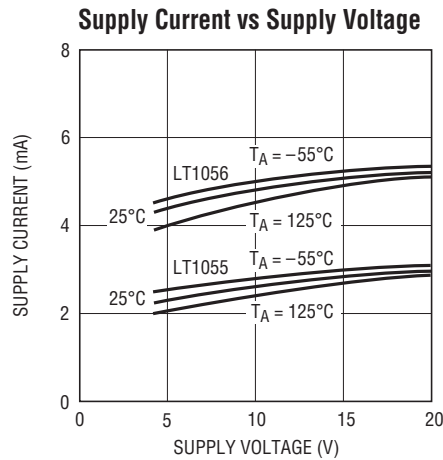
LT1055/56 G23

Power Supply Rejection Ratio vs Frequency



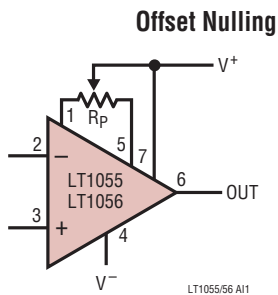
LT1055/56 G24

TYPICAL PERFORMANCE CHARACTERISTICS



APPLICATIONS INFORMATION

The LT1055/LT1056 may be inserted directly into LF155A/LT355A, LF156A/LT356A, OP-15 and OP-16 sockets. Offset nulling will be compatible with these devices with the wiper of the potentiometer tied to the positive supply.



No appreciable change in offset voltage drift with temperature will occur when the device is nulled with a potentiometer, R_P , ranging from 10k to 200k.

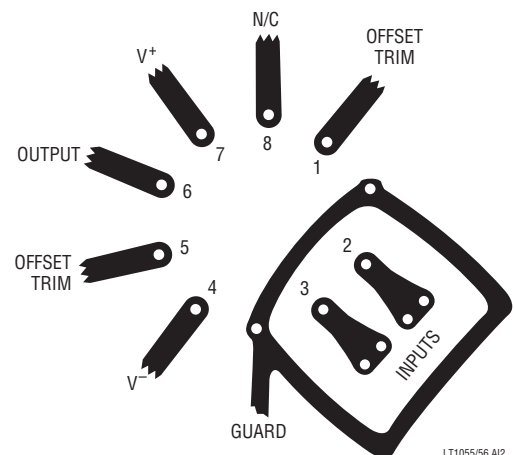
The LT1055/LT1056 can also be used in LF351, LF411, AD547, AD611, OPA-111, and TL081 sockets, provided that the nulling circuitry is removed. Because of the LT1055/LT1056's low offset voltage, nulling will not be necessary in most applications.

Achieving Picoampere/Microvolt Performance

In order to realize the picoampere-microvolt level accuracy of the LT1055/LT1056 proper care must be exercised. For

example, leakage currents in circuitry external to the op amp can significantly degrade performance. High quality insulation should be used (e.g. Teflon, Kel-F); cleaning of all insulating surfaces to remove fluxes and other residues will probably be required. Surface coating may be necessary to provide a moisture barrier in high humidity environments.

Board leakage can be minimized by encircling the input circuitry with a guard ring operated at a potential close to that of the inputs: in inverting configurations the guard ring should be tied to ground, in noninverting connections to the inverting input at pin 2. Guarding both sides of the



APPLICATIONS INFORMATION

printed circuit board is required. Bulk leakage reduction depends on the guard ring width.

The LT1055/LT1056 has the lowest offset voltage of any JFET input op amp available today. However, the offset voltage and its drift with time and temperature are still not as good as on the best bipolar amplifiers because the transconductance of FETs is considerably lower than that of bipolar transistors. Conversely, this lower transconductance is the main cause of the significantly faster speed performance of FET input op amps.

Offset voltage also changes somewhat with temperature cycling. The AM grades show a typical $20\mu\text{V}$ hysteresis ($30\mu\text{V}$ on the M grades) when cycled over the -55°C to 125°C temperature range. Temperature cycling from 0°C to 70°C has a negligible (less than $10\mu\text{V}$) hysteresis effect.

The offset voltage and drift performance are also affected by packaging. In the plastic N8 package the molding compound is in direct contact with the chip, exerting pressure on the surface. While NPN input transistors are largely unaffected by this pressure, JFET device matching and drift are degraded. Consequently, for best DC performance, as shown in the typical performance distribution plots, the TO-5 H package is recommended.

Noise Performance

The current noise of the LT1055/LT1056 is practically immeasurable at $1.8\text{fA}/\sqrt{\text{Hz}}$. At 25°C it is negligible up to 1G of source resistance, R_S (compound to the noise of R_S). Even at 125°C it is negligible to 100M of R_S .

The voltage noise spectrum is characterized by a low $1/f$ corner in the 20Hz to 30Hz range, significantly lower than on other competitive JFET input op amps. Of particular interest is the fact that with any JFET IC amplifier, the frequency location of the $1/f$ corner is proportional to the square root of the internal gate leakage currents and, therefore, noise doubles every 20°C . Furthermore, as illustrated in the noise versus chip temperature curves, the 0.1Hz to 10Hz peak-to-peak noise is a strong function of temperature, while wideband noise ($f_0 = 1\text{kHz}$) is practically unaffected by temperature.

Consequently, for optimum low frequency noise, chip temperature should be minimized. For example, operat-

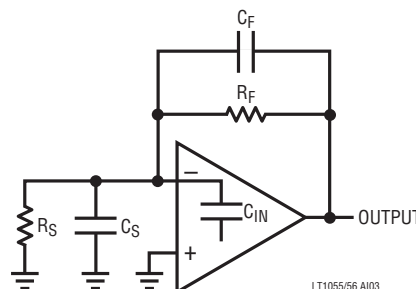
ing an LT1056 at $\pm 5\text{V}$ supplies or with a $20^\circ\text{C}/\text{W}$ case-to-ambient heat sink reduces 0.1Hz to 10Hz noise from typically $2.5\mu\text{V}_{\text{P-P}}$ ($\pm 15\text{V}$, free-air) to $1.5\mu\text{V}_{\text{P-P}}$. Similarly, the noise of an LT1055 will be $1.8\mu\text{V}_{\text{P-P}}$ typically because of its lower power dissipation and chip temperature.

High Speed Operation

Settling time is measured in the test circuit shown. This test configuration has two features which eliminate problems common to settling time measurements: (1) probe capacitance is isolated from the "false summing" node, and (2) it does not require a "flat top" input pulse since the input pulse is merely used to steer current through the diode bridges. For more details, please see Application Note 10.

As with most high speed amplifiers, care should be taken with supply decoupling, lead dress and component placement.

When the feedback around the op amp is resistive (R_F), a pole will be created with R_F , the source resistance and capacitance (R_S , C_S), and the amplifier input capacitance ($C_{\text{IN}} \approx 4\text{pF}$). In low closed-loop gain configurations and with R_S and R_F in the kilohm range, this pole can create excess phase shift and even oscillation. A small capacitor (C_F) in parallel with R_F eliminates this problem. With $R_S (C_S + C_{\text{IN}}) = R_F C_F$, the effect of the feedback pole is completely removed.



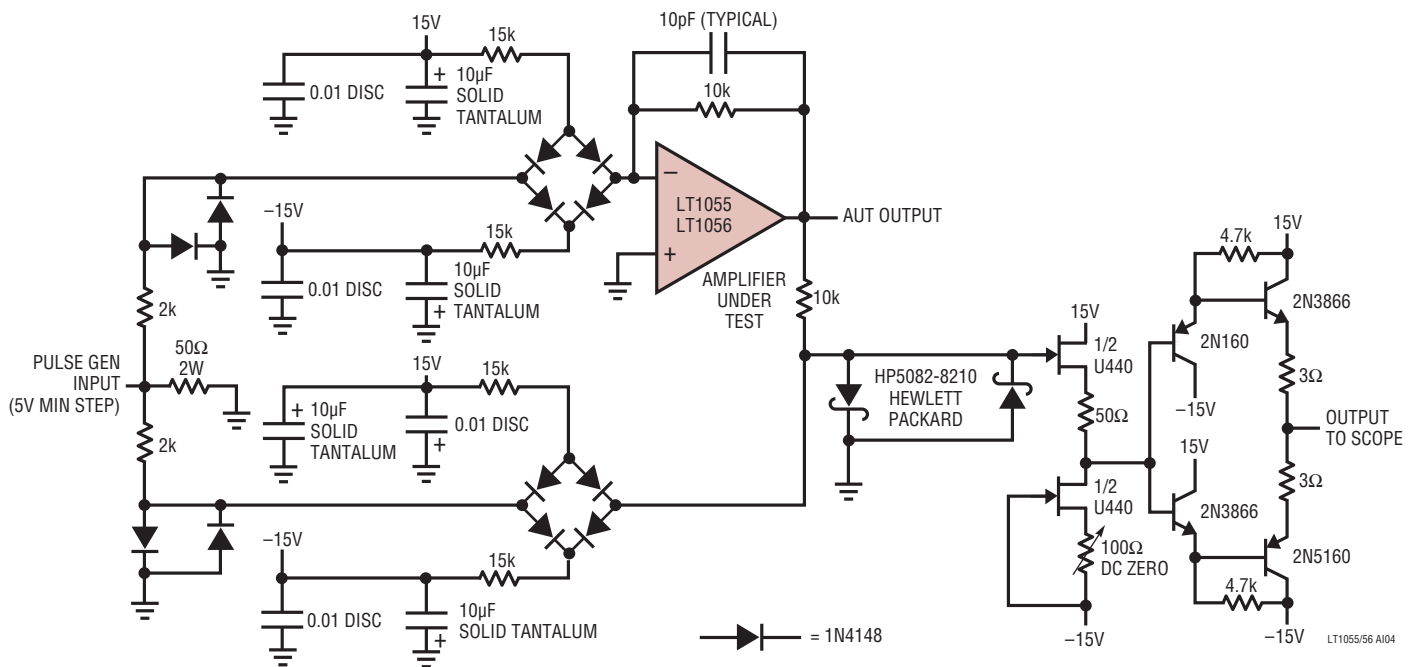
Phase Reversal Protection

Most industry standard JFET input op amps (e.g., LF155/LF156, LF351, LF411, OP15/16) exhibit phase reversal at the output when the negative common mode limit at the input is exceeded (i.e., from -12V to -15V with $\pm 15\text{V}$ supplies). This can cause lock-up in servo systems. As shown below, the LT1055/LT1056 does not have this problem due to unique phase reversal protection circuitry (Q1 on simplified schematic).

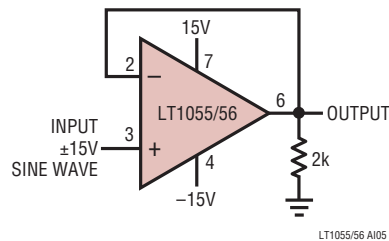
10556fd

APPLICATIONS INFORMATION

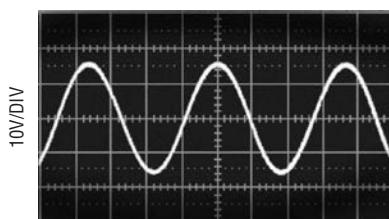
Settling Time Test Circuit



Voltage Follower with Input Exceeding the Negative Common Mode Range

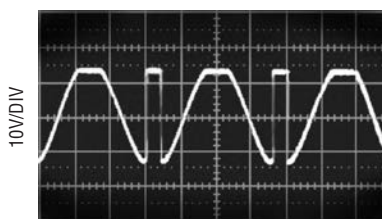


Input



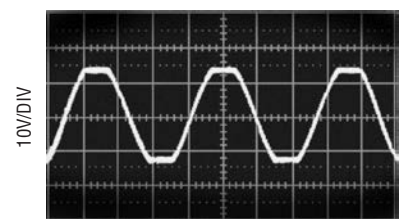
LT1055/56 AI06

Output
(LF155/LF56, LF441, OP-15/OP-16)



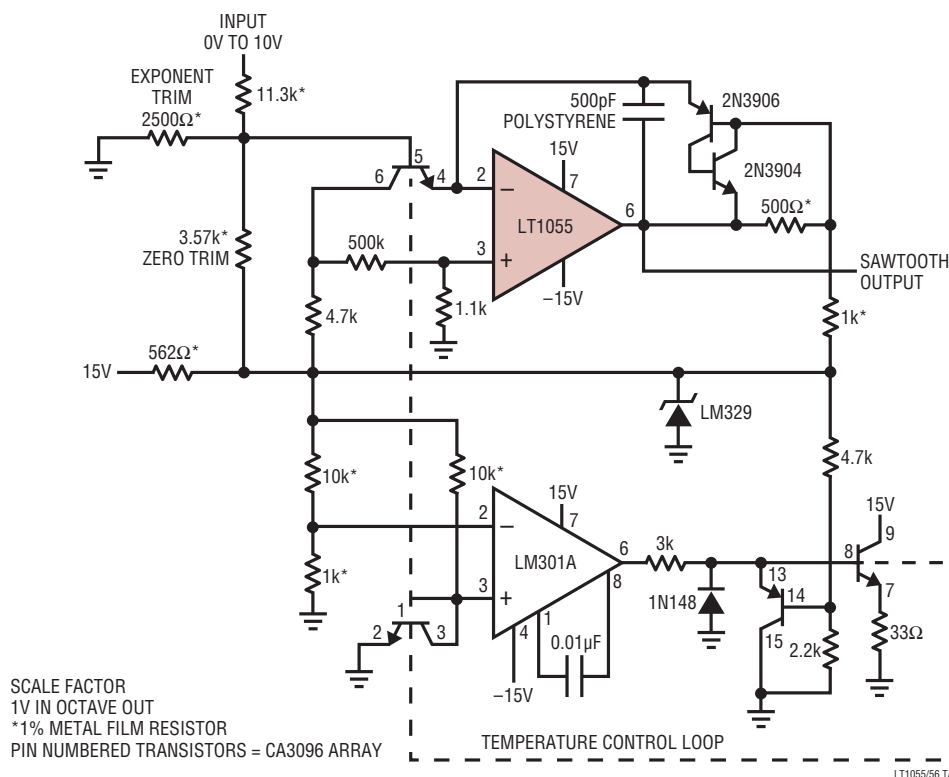
LT1055/56 AI07

Output
LT1055/LT1056



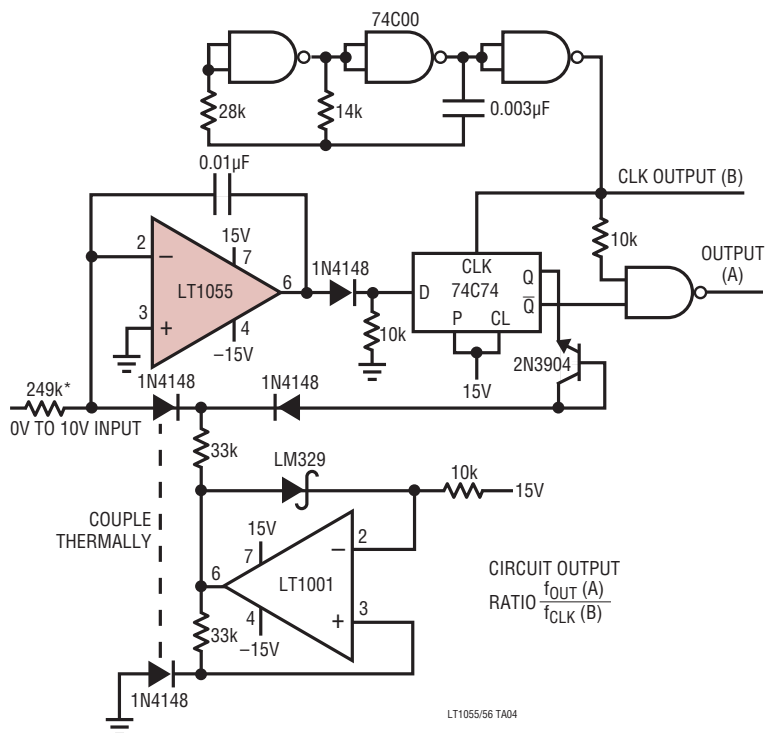
LT1055/56 AI08

Exponential Voltage-to-Frequency Converter for Music Synthesizers



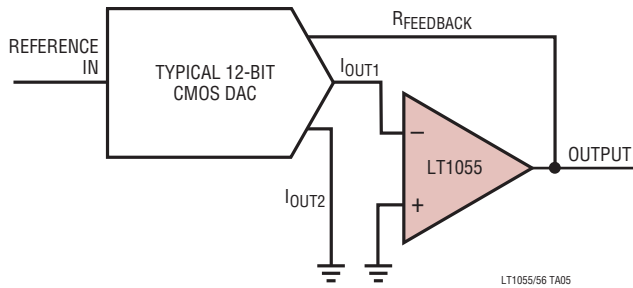
†For ten additional applications utilizing the LT1055 and LT1056, please see the LTC1043 data sheet and Application Note 3.

12-Bit Charge Balance A/D Converter

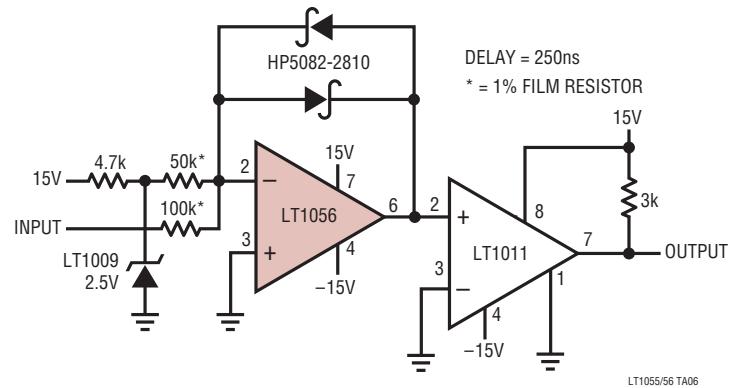


TYPICAL APPLICATIONS

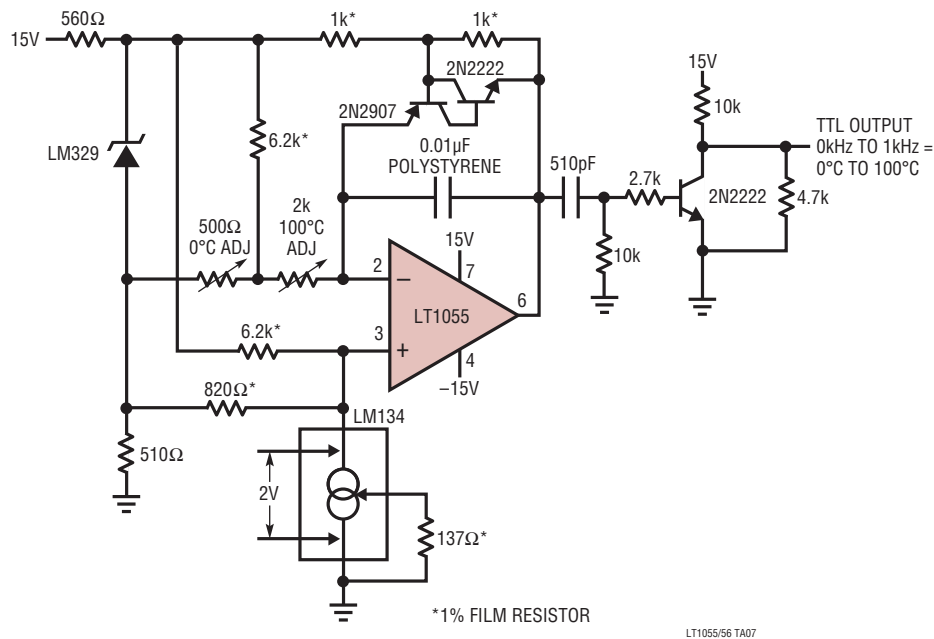
Fast “No Trims” 12-Bit Multiplying CMOS DAC Amplifier



Fast, 16-Bit Current Comparator

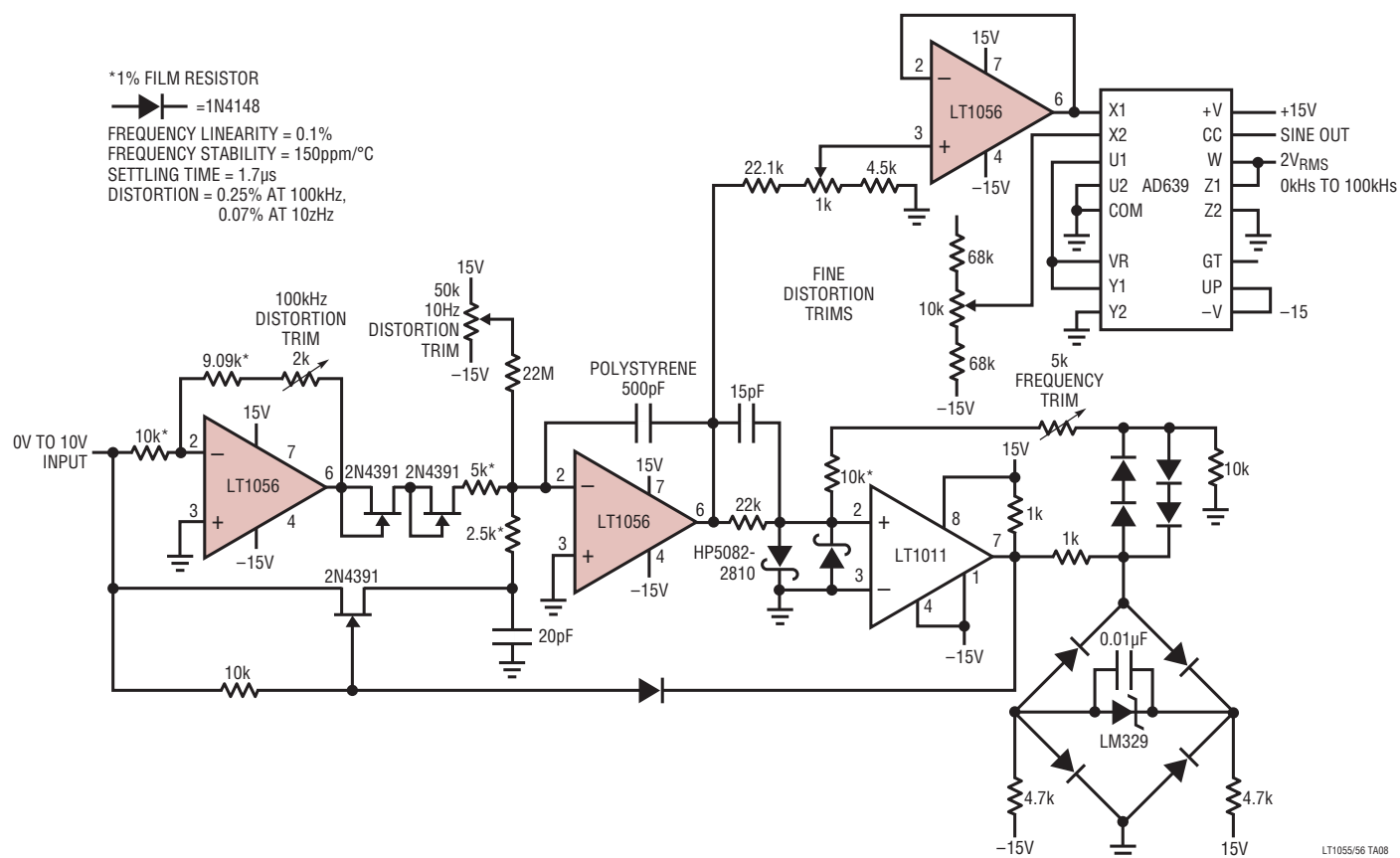


Temperature-to-Frequency Converter

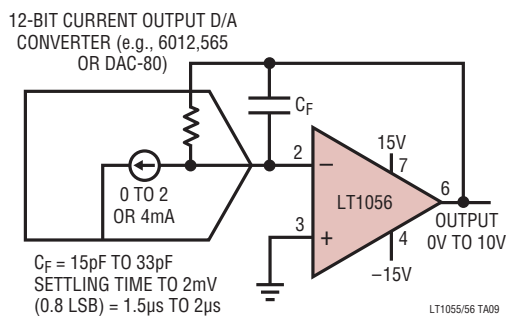


TYPICAL APPLICATIONS

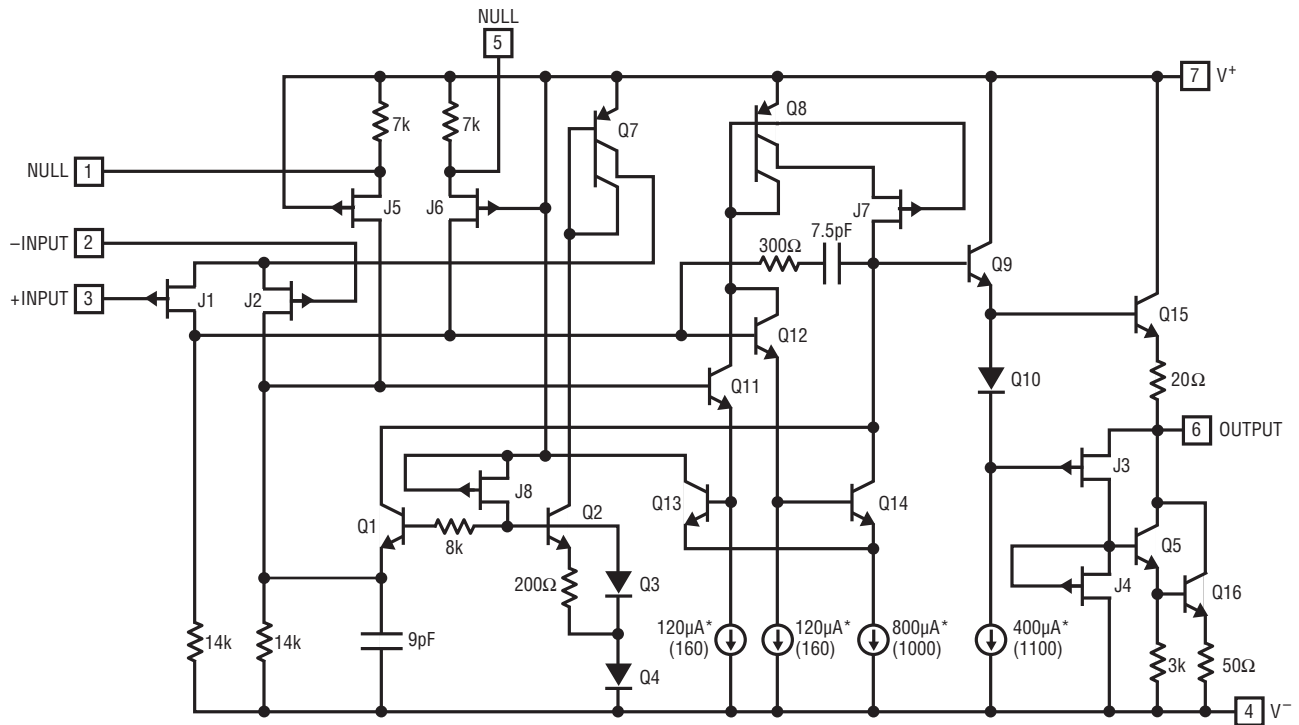
100kHz Voltage Controlled Oscillator



12-Bit Voltage Output D/A Converter



SIMPLIFIED SCHEMATIC

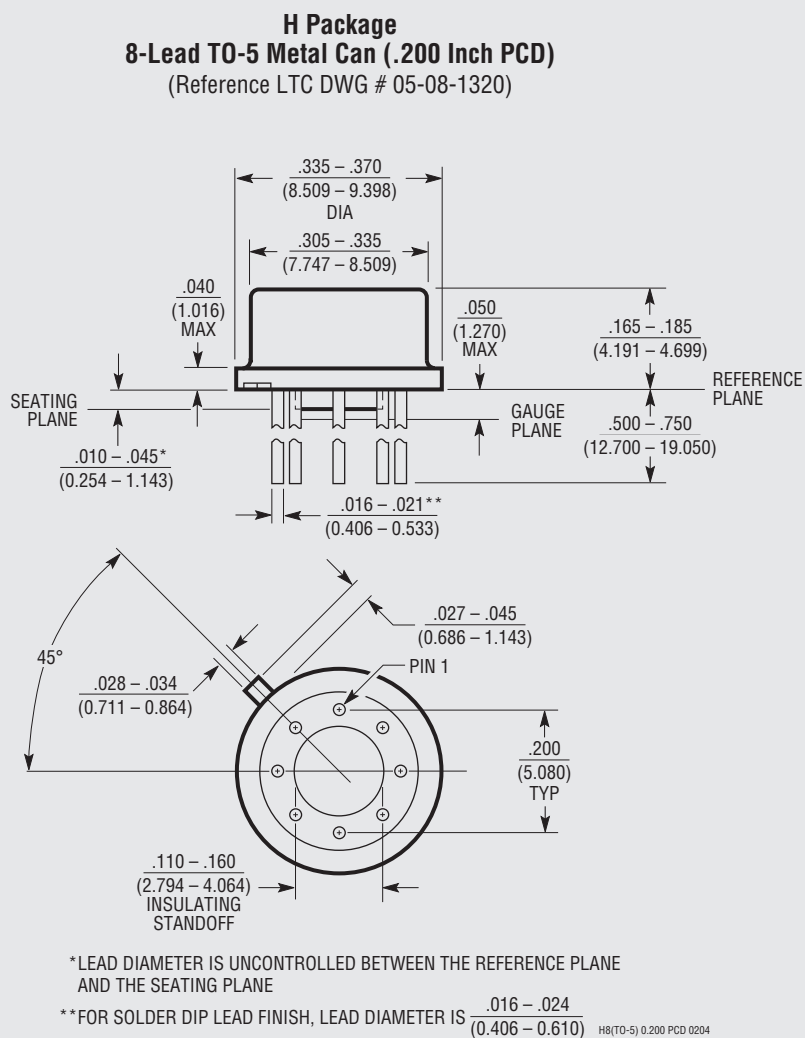


*CURRENTS AS SHOWN FOR LT1055. (X) = CURRENTS FOR LT1056.

LT1055/56 SCHM

PACKAGE DESCRIPTION

Please refer to <http://www.linear.com/designtools/packaging/> for the most recent package drawings.

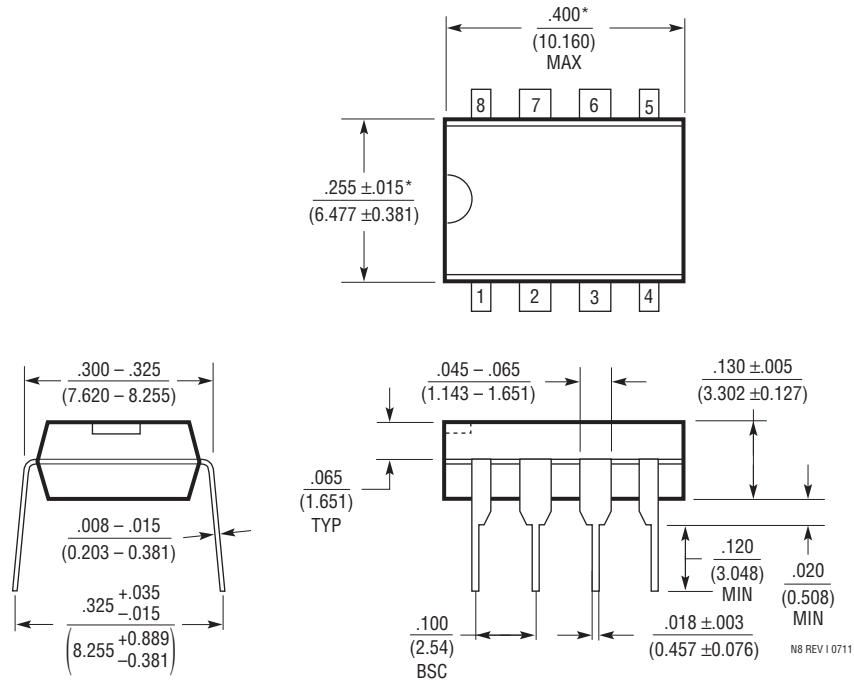


OBSOLETE PACKAGE

PACKAGE DESCRIPTION

Please refer to <http://www.linear.com/designtools/packaging/> for the most recent package drawings.

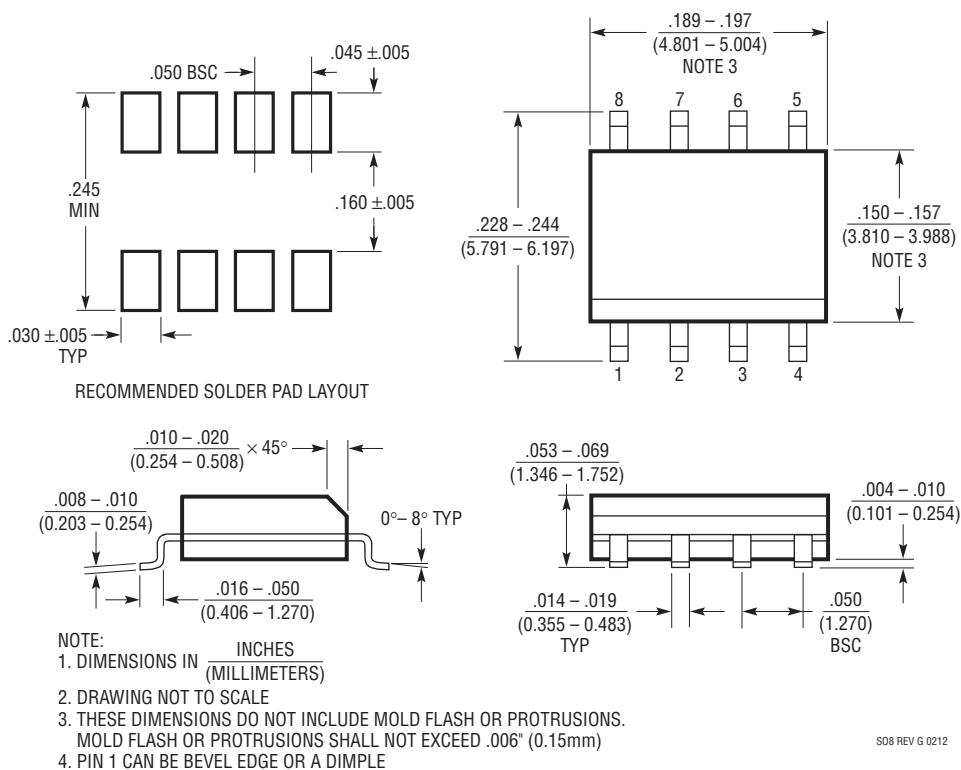
N Package 8-Lead PDIP (Narrow .300 Inch) (Reference LTC DWG # 05-08-1510 Rev I)



PACKAGE DESCRIPTION

Please refer to <http://www.linear.com/designtools/packaging/> for the most recent package drawings.

S8 Package 8-Lead Plastic Small Outline (Narrow .150 Inch) (Reference LTC DWG # 05-08-1610 Rev G)



REVISION HISTORY (Revision history begins at Rev D)

REV	DATE	DESCRIPTION	PAGE NUMBER
D	08/15	Corrected application circuit.	20

The circuit diagram shows an LT1055 op-amp configured as a precision current source. The op-amp's non-inverting input (pin 3) is connected to the INPUT through a 10k resistor. The inverting input (pin 2) is connected to the output (pin 6) through a 100pF capacitor and to ground through a 10k resistor. The op-amp is powered by a 125V supply (pin 1) and a -125V supply (pin 5). The output (pin 6) is connected to a network of resistors and transistors. This network includes a 510Ω resistor, a 330Ω resistor, a 1MΩ resistor, and a 50k resistor. It also features two 1N965 diodes, two 2N5415 transistors, and two 2N3440 transistors. The output of the circuit is labeled OUTPUT. A note indicates that the output is a ±25mA current, and the circuit is designed for use with heat sink output transistors.

RELATED PARTS

PART NUMBER	DESCRIPTION	COMMENTS
LT1122	Fast Settling JFET Op Amp	340ns Settling Time, GBW = 14MHz, SR = 60V/μs
LT1792	Low Noise JFET Op Amp	e _n = 6nV/√Hz Max at f = 1kHz